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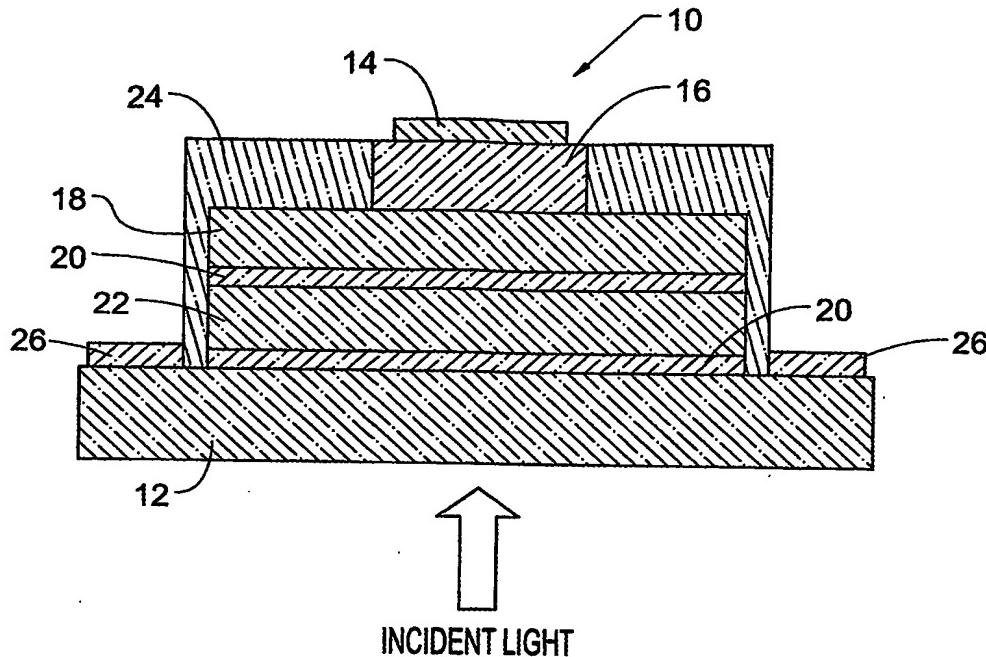
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(54) Title: PIN PHOTODETECTOR



(57) Abstract: A PIN photodetector includes a first semiconductor contact layer, a semiconductor absorption layer having a larger area than the first semiconductor contact layer, a semiconductor passivation layer positioned between the first semiconductor contact layer and absorption layer, and a second semiconductor contact layer. The semiconductor absorption layer and passivation layers are positioned between the first and second semiconductor contact layers.

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